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A bstract. We study the K ondo e ect in a quantum dot coupled to half-metallic ferrom agnetic electrodes in the regime of strong on-dot correlations. Using the equation of motion technique for nonequilibrium G reen functions in the slave boson representation we show that the K ondo e ect is not completely suppressed for antiparallel leads magnetization. In the parallel con guration there is no K ondo e ect but there is an e ect associated with elastic cotunneling which in turn leads to sim ilar behavior of the local (on-dot) density of states (LDOS) as the usual K ondo e ect. N am ely, the LDOS shows the temperature dependent resonance at the Ferm i energy which splits with the bias voltage and the magnetic eld. M oreover, unlike for non-magnetic or not fully polarized ferrom agnetic leads the only minority spin electrons can form such resonance in the density of states. However, this resonance cannot be observed directly in the transport measurem ents and we give som e clues how to identify the e ect in such system s.

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1. Introduction

N ow adays spin dependent phenom ena play in portant role in the m esoscopic system s as they lead to potential applications in nanotechnology (spintronics) [1, 2] and quantum computing [2, 3]. Moreover new transport and thermodynamic phenom ena can be observed in spintronic devices which are associated with the spin of the electron rather than the charge. Those include tunnel magnetoresistance (TMR) in magnetic tunnel junctions [4], spin dependent Andreev re ections [5], non-monotonic behavior of the superconducting transition temperature [6] and spontaneous currents in ferrom agnet – superconductor proximity system s [7] or K ondo e ect [8] in quantum dots (QD) coupled to the ferrom agnetic leads [9]–[27].

The K ondo e ect is a prime example of the many body physics in the quantum dot systems, i.e. form ation of the many body singlet state by the on-dot spin and the conduction electron spins. This state gives rise to the resonance at the Ferm i energy in the QD density of states and zero-bias maximum in di erential conductance. The K ondo e ect was predicted a long time ago [28]-[30], extensively studied theoretically [31]-[34] and con rm ed in series of beautiful experiments [35]-[39] in the QD coupled to the norm al (non-magnetic) leads.

If the norm al leads are replaced by the ferrom agnetic ones, the spin degrees of freedom start to play signi cant role in the transport and therm odynam ic properties of the system, eventually leading to new phenom ena. One of such new e ects is the splitting of the K ondo resonance [12, 18, 19, 20, 25, 26] due to the spin dependent quantum charge uctuations induced by the tunneling between QD and spin polarized leads. Rem arkably it is possible to recover the full K ondo e ect (no splitting) by applying of the external m agnetic eld [12, 19, 25, 26]. The splitting of the K ondo resonance strongly depends on the alignment as well as on the magnitude of the lead magnetizations. In particular when the magnetizations in both leads point in opposite directions (anti-parallel alignment), the full equilibrium K ondo e ect survives for all values of the polarizations and there is no splitting of the zero energy resonance. In the di erential conductance however the zero bias resonance is getting sm aller and sm aller as the leads become more polarized, nally leading to complete disappearance of the K ondo anomaly. On the other hand, in parallel con guration (magnetizations in both leads are parallel to each other) the K ondo resonance is split and gets suppressed when the magnitude of the polarization is being increased.

The presence of ferrom agnetism in the electrodes can also lead to the quantum critical point with non-Ferm i liquid behavior. It was shown recently [40] that the competition of spin waves (collective low energy excitations in a ferrom agnet) and the K ondo e ect is responsible for such a behavior. In this case the critical K ondo e ect manifests itself in a fractional power law dependences of the conductance on temperature, and AC conductance and therm al noise on frequency !. Thus the QD system with ferrom agnetic electrodes can help us to understand the quantum critical phenom ena in heavy ferm ions and other correlated electron system s.

In the present paper we show that if the leads are fully polarized, so the density of states in the leads is non-zero for one electron spin direction only, there is the K ondo e ect, provided leads are in anti-parallel magnetization con guration. On the other hand in the parallel con guration there is no usual K ondo e ect but there is an e ect associated with elastic cotunneling which leads to similar behavior of density of states as in usual K ondo e ect. M oreover, this e ect occurs only in the minority spin electron channel when there is an unpaired spin on the dot and strong on-dot C oulom b interactions, i.e. when QD is in the C oulom b blockade regim e.

The paper is organized as follows: in the Sec. 2 theoretical description of the QD coupled to the external leads is presented. Sec. 3 is devoted to various elastic and inelastic cotunneling processes in the case of half-m etallic leads. In the rest of the paper the num erical results concerning the density of stets (Sec. 4), applying of the external m agnetic eld (Sec. 5) and the transport properties (Sec. 6) are discussed, and nally, som e conclusions are presented in the Sec. 7.

2. The M odel

Our system under consideration is represented by the single in purity Anderson model H am iltonian in the lim it of strong on-dot C oulom b interaction (U ! 1) in the slave boson representation where the real on-dot electron operator d is replaced by the product of the boson b and the ferm ion f operators (d = b⁺ f) [41, 42]:

$$H = \sum_{k}^{X} c_{k}^{+} c_{k} + \prod_{k}^{T} f_{k}^{+} f_{k} + \sum_{k}^{X} V_{k} c_{k}^{+} b_{k}^{+} f_{k}^{+} + H c;; (1)$$

where c_k stands for the electrons with the single particle energy $_k$, the wave vector k and the spin in the lead = L;R. " denotes the dot energy level and V $_k$ is the hybridization matrix element between the electrons on the dot and those in the leads.

W ithin the Keldysh formalism [43], the total current I = I owing through the quantum dot is given in the form :

$$I = \frac{e^{X}}{2} d! \frac{L(!)_{R}(!)}{L(!) + R(!)} [f_{L}(!) - f_{R}(!)] (!);$$
(2)

where we have introduced the elastic rate $(!) = {P \atop k} \mathbf{j} \mathbf{j}_k \mathbf{j}'$ $(! \atop k)$, and (!) is the spectral function of the dot retarded G reen's function $G^r(!)$, calculated within the equation of motion technique (EOM) in the slave boson representation [34, 44].

As is well known the EOM technique is reliable in the high temperature regime, however it also qualitatively captures the K ondo physics [34]. Moreover the EOM is the one of very few techniques which allows to study nonequilibrium properties of the spin polarized QD system.

W ithin this approach the dot retarded G reen's function reads:

$$G^{r}(!) = \frac{1 \text{ hn } i}{! ! 0 (!) _{I}(!) + i0^{+}}; \qquad (3)$$

with non-interacting (U = 0)

$$_{0} (!) = \frac{X}{k} \frac{\frac{1}{V} \frac{2}{k}}{!};$$
(4)

and interacting self-energy

$$I_{I}(!) = \frac{X_{k}}{!} \frac{J_{k}}{!} \frac{J_{$$

which is responsible for the generation of the K ondo e ect. In i is the average occupation on the QD, calculated under nonequilibrium within the standard scheme [34, 44].

To get the splitting of the K ondo resonance in the presence of the ferrom agnetic leads we follow Ref. [12] and replace " on the r.h.s. of the Eq. (5) by ", which is found from the self-consistency relation

$$\mathbf{u} = \mathbf{u} + \operatorname{Re}[_{0}(\mathbf{u}) + _{I}(\mathbf{u})];$$
 (6)

In numerical calculations we have chosen = P = 1 as an energy unit. The magnetization in the lead is de ned as $p = \frac{*}{*} + \frac{*}{*}$. For half-m etallic leads (HM) we have $_{L^{"}} = _{R^{"}} = 0.5$ and $_{L^{\#}} = _{R^{\#}} = 0$ in the parallel con guration, while $_{L^{"}} = _{R^{\#}} = 0.5$ and $_{L^{\#}} = _{R^{"}} = 0$ in the anti-parallel con guration.

3. Tunneling processes

Before the presentation of the numerical results let us discuss various tunneling processes, associated with the second generation of G reen functions obtained in the EOM procedure. They are the second order processes in the hybridization and describe elastic and inelastic cotunneling. The cotunneling is a process which leaves the charge on the dot unchanged. M oreover, elastic cotunneling does not change spin on the dot either, thus it leaves the dot in its ground state. On the other hand, the inelastic one changes the ground state [45].

As is well known the EOM approach is a non-perturbative technique, and one cannot assume that those processes are fully taken into account. They are rather incorporated in the calculations only qualitatively. It should be stressed that they are likely not the only processes as one may get the other processes of the same order or contributions to the ones discussed here, while going further in EOM procedure, i.e. calculating higher generation GFs. Unfortunately, an exact solution of the model is not known, and for the present purposes it is enough to consider those, shown in Fig. 1.

In Fig. 1 we show such elastic and inelastic single barrier (left panels) and double barrier (right panels) cotunneling processes which start from the spin up electron in the lead L and spin down electron on the dot (C oulomb blockade regime). There are also processes which start from lead R and can be obtained by replacing L ! R. In general, for not fully polarized leads there are processes for opposite spins (!) but in the case of half-m etallic ferrom agnetic leads in parallel con guration they are not allowed

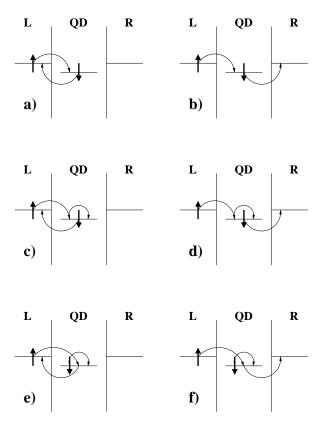


Figure 1. Various tunneling processes associated with second generation G reen functions in the present EOM approach. For simplicity we have shown only processes starting from the left electrode. The remained ones can be obtained by replacing L! R (see discussion in the text. Left panels show single barrier cotunneling and ! and right panels - double barrier cotunneling events. Panels a) and b) show usual inelastic cotunneling, leading to the K ondo e ect, changing the spin on the dot and in one or both electrodes. c) and d) are sim ilar to a) and b) with additional annihilation and creation of the spin on the dot. All above processes change spin on the dot and in the lead (s). The processes displayed in panels e) and f) lead to the same nal spin state on the dot (elastic cotunneling). In general the only processes contributed to the current across the dot are associated with double barrier cotunneling, displayed in panels b), d) and f). In the case of halfm etallic ferrom agnetic leads in the antiparallel con quration the allowed processes are those in b), d) and e), but they do not contribute to the current, while in parallel con guration they are those displayed in e) and f) with the only f) giving a contribution to the current.

due to lack of the density of states for m inority spin electrons in the leads. W e do not show the processes with the same spins on the dot and in the lead, as well as those with empty dot state.

Panels a) and b) show the processes in which the electron with spin up tunnels from the lead L onto the dot and the electron with spin down tunnels from the dot into the lead L (a)) or R (b)), describing inelastic cotunneling and leading to the usual K ondo e ect, as the spin on the dot is changed. Sim ilar situation is displayed in c) and d), namely, the dot starts with spin down and ends with spin up. However, during this

tunneling event, additionally, the spin up electron on the dot is annihilated and created. Those are renorm alized inelastic cotunneling processes. In all above processes the spin on the dot and in the lead (s) is ipped, so those are the K ondo related processes. There are two more processes, shown in e) and f), in which there is no spin ip. The process starts with spin up in the lead L and ends with the same spin in lead L (e)) or R (f)). Similarly, the initial and the nal spin state on the dot remains the same. Thus they describe also renorm alized but elastic cotunneling, as the ground state remains unchanged. B oth processes lead, as we shall see later on, to similar main features of the dot density of states as in usual K ondo e ect.

As one can read o from Fig. 1, all the processes are allowed only if the leads are not polarized (param agnetic) or not fully polarized. Moreover, the only processes contributed to the current across the dot are double barrier cotunneling processes, shown in b), d) and f).

In the case of the halfmetallic ferrom agnetic leads in anti-parallel (AP) con guration, the allowed processes are those shown in b), d) and e). However, they do not give any contribution to the current. In fact, processes b) and d), as they describe double barrier cotunneling, allow for the tunneling but once the electron with the spin down tunnels o the dot into the lead R, the spin up electron can tunnel from the lead L onto the dot and the further tunneling is blocked. The only possibility is the opposite process, namely, the spin up electron tunnels from the dot into the lead R and the spin down electron from the lead R tunnels onto the dot. Thus, in this case the electron transport is completely blocked. The process shown in e) also does not contribute to the current as in this case the electron starts and ends in the same lead (single barrier cotunneling). As a result, in the case of AP con guration there is no current through the quantum dot.

On the other hand, in the case of the half metallic leads in parallel (P) conguration there is one process giving a contribution to the current. This is the process shown in Fig. 1f), coming from the Coulomb interaction. In this case the process starts with spin up in the lead L and ends with the same spin in the lead R, thus not changing the ground state (double barrier elastic cotunneling). Note that the inelastic cotunneling is not allowed in this case. This process at zero temperature has a mite probability in the Coulomb blockade only, i.e. when the dot energy level is below the Ferm i energy of the electrodes, and there is strong on-dot C culomb interaction. M oreover, this process is allowed only when the dot is occupied by spin down electron. It gives a non-zero contribution to the dot density of states below the Ferm i level (shifted by "_{*} "_# in the parallel conguration) only (see Fig. 2 (bottom panel) and Fig. 4 (top panel)). It is shown in the next section that this process leads to sim ilarm ain behavior of the density of states of the dot as the usual K ondo elect.

4. Density of states

In the Fig. 2 we show the spin resolved nonequilibrium ($_{\rm R} = _{\rm L} = 0.2$) density of states (DOS) of the quantum dot coupled to the external leads. Top panel shows

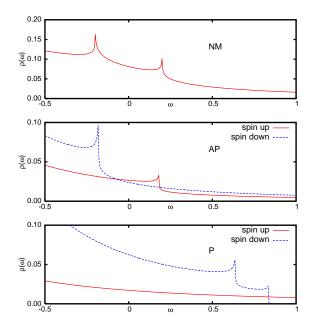


Figure 2. Nonequilibrium ($_{\rm R} = _{\rm L} = 0.2$) density of states of the quantum dot coupled to non-magnetic (top panel), half-m etallic leads in anti-parallel con guration (middle panel) and in parallel con guration (bottom panel). The solid (dashed) line shows the spin up (down) electron DOS. The model parameters are: " $_{\rm m} = "_{\#} = 2$, T = 10³. All energies are measured in units of .

the usual DOS of the QD with non-magnetic (NM) leads where two Abrikosov-Suhl resonances located at the chemical potentials of the leads can be observed. The middle panel displays the DOS of the QD coupled to the half metallic electrodes in anti-parallel (AP) conguration ($p_L = p_R = 1$). It is worthwhile to note that we have now spin up K ondo resonance at $! = _R$ (solid line) and no resonance at $! = _L$. In this case the spin up on the dot is screened by the spins down in the lead R ($_{R\#} \in 0$). For spin down electrons situation is opposite, the spin down on the dot is screened by the spins up in the lead L ($_{L''} \in 0$) and therefore there is a resonance for $! = _L$ and lack of it for $! = _R$. This is di erent from general case of p < 1, where two resonances at both chemical potentials are present (sim ilarly as in non-magnetic case) [12].

Situation is quite di erent in the parallel (P) con guration ($p_L = p_R = 1$) where the spin up DOS (solid line in the bottom panel of the Fig.2) shows no signatures of the K ondo e ect as the spin up on the dot cannot be screened by spins down in either lead ($_{L\#} = _{R\#} = 0$). However, in the spin down channel the residual K ondo-like state can be produced due to the processes shown in the Fig.1e) and f). This manifests itself in two resonances in the DOS located at ! = "+" (see dashed line in the bottom panel of the Fig.2), where "= "," "_# is the splitting due to the ferrom agnetic leads. Such splitting has been also observed in general case of FM (p < 1) leads, where the charge uctuations play signi cant role, i.e. when $2j'_d j \in U$ [12, 19, 20]. Note that in AP con guration there is no such splitting, again, in agreement with general case of p < 1 polarization [12, 19, 20].

Another important e ect is a cuto of the one of the resonances at the energy $! = "+ _{R}$. This indicates that there is no direct tunneling of the spin down electrons and the resulting density of states com es form the virtual processes shown in Fig. 1e) and f) only, as discussed in Sec. 3.

Figure 3 shows the low temperature dependence of the full width at the half maximum (FW HM) of the narrow (K ondo) resonance in the density of states near $!_{K}$, which equals to the Ferm i energy ($_{L} = _{R} = 0$) when QD is coupled to the non-magnetic or half-m etallic leads in AP con guration and $!_{K} = "$ for half-m etallic leads in AP con guration and $!_{K} = "$ for half-m etallic leads in P con guration. The points with errorbars show num erically found values of the

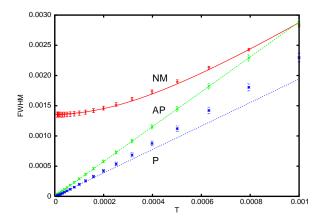


Figure 3. The low temperature behavior of the full width at the half maximum (FW HM) of the narrow (K ondo) resonance in NM, AP and P con gurations.

FW HM. The K ondo tem peratures in all cases have been found by tting the function $FW HM = {}^{P} \frac{1}{T_{K}^{2} + aT^{2}}$ to those points. In th NM case it gives $T_{K} = 1.36 \quad 10^{3}$ while in the AP $-T_{K} = 1.07 \quad 10^{5}$. The lower T_{K} in AP conguration steams from the fact that the K ondo state in this case is formed by the electron spins in one lead only for a given direction of the spin on the dot. In the P conguration T_{K} is equal to zero as in this case there is no K ondo elect. Moreover in the P conguration the FW HM signi cantly deviates from the linear behavior for higher temperatures. On the other hand in the NM and AP congurations it is still linear above $T = 10^{2}$ (not shown in the Fig. 3).

5. Compensation by the external magnetic eld

Now, the question arises if the residual K ondo-like e ect in P con guration can be compensated by the external magnetic eld B. C ompensation in this case means no splitting of the dot energy levels " = 0. In the Fig. 4 we show the equilibrium ($_{\rm L} = _{\rm R} = 0$) spin down (top panel) and spin up (bottom panel) density of states

for dierent values of Beld. As it is evident, magneticeld shifts the spin down

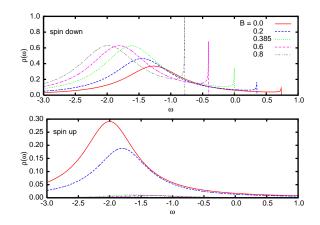


Figure 4. Equilibrium ($_{\rm L} = _{\rm R} = 0$) spin down (top panel) and spin up (bottom panel) density of states for various values of the external magnetic eld indicated in the gure. At B = B_{com p} = 0:385 there is no splitting of the dot energy level, thus the K ondo e ect is compensated. Note strong suppression of the spin up density of states for B _{B_{com p}.}

K ondo resonance and at $B = B_{comp} = 0.385$ it reaches the Ferm i energy. No splitting " is observed in this case. Note that the K ondo resonance rapidly grows as B eld is increased while the broad resonance around the dot energy level initially also grows up but for $B > B_{comp}$ remains almost unchanged (position of it changes only). The spin up density of states (bottom panel) shows di erent behavior. Namely, the broad charge uctuation resonance starts to decrease with increasing of the B eld and at $B = B_{comp}$ is remarkably small. This e ect is associated with the change of the average occupation for di erent spin directions on the dot (hn i). When the B eld increases, ", moves towards the Fermi energy while ", moves in opposite direction and therefore hn_*i decreases while hn_*i increases its value. This is clearly seen in the Fig. 5, where the occupations of the dot for both spin directions are shown. As one can see the spin up (down) occupation number decreases (increases) with the increasing of the external magnetic eld B. As soon as the B eld exceeds $B_{comp} = 0.385$, so one can think in this case about overcom pensated residual K ondo-like e ect, both occupation num bers remain almost constant, strictly speaking, they change very slow ly towards 1 in the spin down channel (fully occupied state) and 0 in the spin up channel (empty state).

Corresponding non-equilibrium density of states for di erent magnetic elds is shown in Fig. 6. While the behavior is similar to that shown in Fig. 3, except the fact that there are two resonances now, one can see larger spin up density of states at $B = B_{comp}$. This is simply due to the smaller value of the spin down electron occupation number.

A swe have seen the residual K ondo-like e ect can be compensated by the external magnetic eld. However, the compensation in this case means something di erent than in general case of p < 1. First of all, we have to remember that there is only one

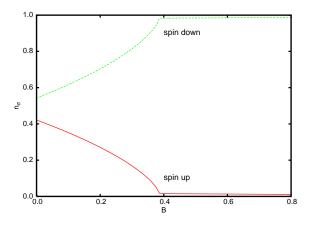


Figure 5. Evolution of the average spin dependent occupation number with the external magnetic eld B.N ote that with increasing of the B eld the spin polarization (di erence between the occupation of the spin up and the spin down electrons) also increases and remains almost constant (changes very slow ly) for $B > B_{comp} = 0.385$.

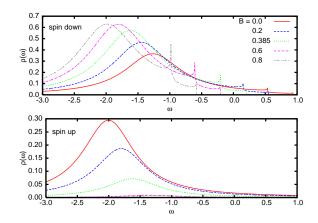


Figure 6. Non-equilibrium ($_{\rm L} = _{\rm R} = 0.2$) spin down (top panel) and spin up (bottom panel) density of states for the same values of the external magnetic eld as in Fig. 3.

resonance (for one spin direction only) in the DOS, which can be shifted to the Ferm i energy by the external magnetic eld. This is what we call the compensation. In general case of p < 1 there are two resonances (for both spin directions) in the DOS, which can be moved to the Ferm i energy. Moreover, as it has been shown [12, 19], the occupations for both spin directions become equal at $B = B_{comp}$ - there is no spin polarization for such external magnetic eld. In the case of HM (p = 1) leads, there is non-zero spin polarization, i.e. $hn_{\#}i \in hn_{\#}i$ (see the Fig.5). Consequently, the spin on the dot cannot be fully screened by the spins in the leads, and there is no K ondo e ect in the common sense. This is the main and important di erence between the compensation e ect in the case of HM and FM (p < 1) leads.

Finally, we would like to comment on the compensation of the K ondo e ect in general case of the p < 1 within the present approach and compare it to the other

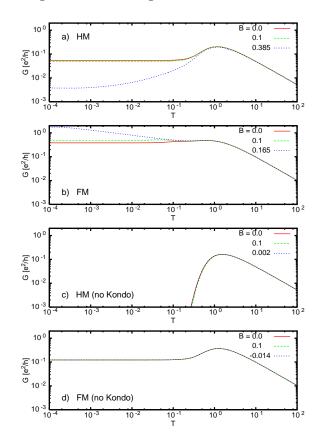
works known in the literature [12, 19, 20]. The obtained results and the conclusions are qualitatively the same as in the papers mentioned above. However, the values of the $B_{com\,p}$ in the present work di ers from those in Ref. [12] due to the fact that we have assumed spin dependent bandwidths in electrodes in order to have the densities of states in the leads norm alized to 1. For this reason our approach gives the values of the $B_{com\,p}$ sm aller than those of Ref. [12], also obtained within EOM technique. W ithout this norm alization requirement we get perfect quantitative agreement with that approach.

All this shows clear evidence of the usual K ondo e ect in the DOS of the quantum dot coupled to the halfm etallic ferrom agnets in AP con guration and sim ilar cotunneling related e ect in P con gurations. In both cases the density of states shows the splitting of the zero energy resonance caused by the nonequilibrium conditions ($_{\rm L} \in _{\rm R}$) or the exchange eld coming from the electrodes in P con guration and nally the compensation of it by the external magnetic eld. Unfortunately, it is not possible to measure directly the density of states in transport experiments and the problem arises how to con m this e ect experimentally. In AP con guration there is K ondo e ect for both spin directions but the tunneling current is zero in both cases due to the product of $_{\rm L}$ (!) $_{\rm R}$ (!) (see Eq.(2)), which vanishes (see also discussion in the previous section). On the other hand, in P con guration the cotunneling related e ect is present for minority spin electrons but there is no density of states in the electrodes for this spin direction. H opefully, in this case presence of the e ect in the minority electron duannel m odi es also the transport properties in the other duannel, therefore in general it is possible to get som e inform ation on this e ect.

6. Transport properties

Figure 7 shows the tem perature dependence of the linear conductance $G = \frac{dI}{dV} j_{y \downarrow 0}$ for di erent values of the external magnetic eld B. At zero magnetic eld conductance of QD coupled to the half-m etallic leads is alm ost constant at low tem peratures (panela)), similarly as for QD with ferrom agnetic leads where the polarization is p = 0.3 (panel b)). When Beld increases, G of HM starts do decrease, unlike for FM system, where it grows up, and nally the K ondo e ect is fully compensated at B $_{comp} = 0.165$. In HM system at B = B_{comp} = 0:385 (note that B_{comp} are dierent in HM and FM system s, simply due to di erent lead polarizations), the conductance decreases with T and at low temperatures is an order of magnitude smaller than at B = 0. The decrease of G is related to the suppression of the DOS in majority spin channel, as it can be read o from the Fig. 4. Such behavior of the conductance remains in agreement with the results obtained within numerical renormalization group technique (see the Fig. 4b) of Ref. [19]), where G is plotted as a function of the polarization for $B = B_{comp}$. For alm ost all values of the polarizations p the conductance is equal for both spin directions, except for p close to 1, where the G becomes spin polarized. In our case of p = 1, the conductance is fully polarized, as the only one spin channel contributes to the transport.

We have also calculated G in HM (panel c)) and FM (d)) system without elastic



F igure 7. The linear conductance as a function of the tem perature for the quantum dot coupled to the half-m etallic a) and ferrom agnetic leads b) with polarization p = 0.8. Note di erent behavior with respect to the external magnetic eld. For ferrom agnetic leads b) it is possible to get usual K ondo e ect by tuning of the magnetic eld. For half-m etallic leads applying of the magnetic eld $B = B_{com p}$ suppresses the conductance. Panels c) and d) show the same as a) and b) respectively with neglected cotunneling like correlations.

cotunneling and K ondo like correlations taken into account, neglecting interacting selfenergy $_{\rm I}$ (!) in Eq.(3), which corresponds to skipping of all tunneling processes shown in the Fig. 1. It is clearly seen that the whole low temperature contribution to the conductance of QD with HM leads is due to the renorm alized elastic cotunneling processes and therefore we can conclude that non-zero G is a signature of this e ect. C onductance of QD coupled to FM leads without cotunneling correlations (panel d)) shows similar behavior as G for HM leads with those processes (panel a)) at B = 0. However, lack of the B dependence in this case can easily distinguish it from general case of QD coupled to HM leads. Therefore, such spectacular behavior of the conductance of the QD with HM leads can be, in general, possible to observe in transport measurem ents.

Additional insight into the problem can be reached from the behavior of the di erential conductance vs bias voltage $eV = L_R$, displayed in the Fig. 8. As one can see in the gure (panel a)) there are temperature dependent sm all kinks at eV = -. For comparison the di erential conductance of QD coupled to FM electrodes

7.Conclusions

In conclusion we have studied the properties of the quantum dot coupled to the halfm etallic leads. In the case of parallel con guration, the e ect associated with elastic cotunneling, which leads to similar behavior of the density of states, can be observed. The density of states shows the splitting of the zero energy resonance caused by the nonequilibrium conditions ($_{\rm L} \in _{\rm R}$) or the exchange eld coming from the electrodes and nally the compensation of it by the external magnetic eld. However the compensation means the shift of the resonance (in the DOS) to the Ferm i energy only, without additional conditions of equal occupations and equal conductances for both spin directions, as in the case of p < 1. This e ect can be observed experimentally measuring the temperature dependence of the linear and di erential conductances in the external magnetic eld. On the other hand, in the case of AP con guration, the DOS shows usual K ondo e ect but the transport is completely suppressed.

A cknow ledgm ents

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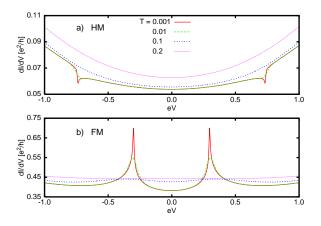


Figure 8. Dierential conductance dI=dV of the QD coupled to HM a) and FM b) electrodes for various tem peratures.

References

- [1] G.A. Prinz, Science 282, 1660 (1998).
- [2] Sem iconductor Spintronics and Quantum Computation, ed.D.Awschalom, D.Loss, D.Sam arth, Springer, New York (2002).
- [3] D.Loss, D.P.D iV incenzo, Phys. Rev. A 57, 120 (1998).
- [4] Spin Dependent Transport in Magnetic Nanostructures, ed. S. Maekawa, T. Shinjo, Taylor & Francis, London and New York (2002).
- [5] M.J.M.de Jong, C.W.J.Beenakker, Phys. Rev. Lett. 74, 1657 (1995).
- [6] Y.A. Izyum ov, Y.N. Proshin, M.G. Khusainov, Phys. Usp. 45, 109 (2002).
- [7] M.Krawiec, B.L.Gyor y, J.F.Annett, Phys. Rev. B 66, 172505 (2002); Eur. Phys. J.B 32, 163 (2003); Physica C 387, 7 (2003); Phys. Rev. B 70, 134519 (2004).
- [8] A.C.Hewson, The Kondo Problem to Heavy Fermions, Cambridge University Press, Cambridge, (1993).
- [9] A.N.Pasupathy, R.C.Bialczak, J.Martinek, J.E.Grose, L.A.K.Donev, P.L.McEuen, D.C. Ralph, Science 306, 85 (2004).
- [10] J.Nygard, W.F.Koehl, N.Mason, L.DiCarlo, C.M.Marcus, cond-mat/0410467.
- [11] N.Sergueev, Q.F.Sun, H.Guo, B.G.W ang, J.W ang, Phys. Rev. B 65, 165303 (2002).
- [12] J. Martinek, Y. Utsum i, H. Imamura, J. Barnas, S. Maekawa, J. Konig, G. Schon, Phys. Rev. Lett. 91, 127203 (2003).
- [13] R.Lu, Z.-R.Liu, cond-m at/0210350.
- [14] P.Zhang, Q.K.Xue, Y.P.W ang, X.C.X ie, Phys. Rev. Lett. 89, 286803 (2002).
- [15] J.Ma, B.Dong, X.L.Lei, Commun. Theor. Phys. 43, 341 (2005).
- [16] B.R.Bulka, S.Lipinski, Phys. Rev. B 67, 024404 (2003).
- [17] R.Lopez, D.Sanchez, Phys. Rev. Lett. 90, 116602 (2003).
- [18] B.Dong, H.L.Cui, S.Y.Liu, X.L.Lei, J.Phys.: Condens. M att. 15, 8435 (2003).
- [19] J. Martinek, M. Sindel, L. Borda, J. Barnas, J. Konig, G. Schon, J. von Delft, Phys. Rev. Lett. 91, 247202 (2003).
- [20] M.-S.Choi, D.Sanchez, R.Lopez, Phys. Rev. Lett. 92, 056601 (2004).
- [21] J.Ma, X.L.Lei, Europhys.Lett. 67, 432 (2004).
- [22] J.Konig J.Martinek, J.Barnas, G.Schon, CFN Lectures on Functional Nanostructures, Eds.K. Busch et al., Lecture Notes in Physics 658, Springer, 145 (2005).
- [23] J. Martinek, M. Sindel, L. Borda, J. Barnas, R. Bulla, J. Konig, G. Schon, S. Maekawa, J. von Delft, cond-mat/0406323.
- [24] Y. Tanaka, N. Kawakami, J. Phys. Soc. Japan 73, 2795 (2004).
- [25] D. Sanchez, R. Lopez, M. -S. Choi, J. Supercond. 18, 251 (2005).
- [26] Y. Utsum i, J. Martinek, G. Schon, H. Im am ura, S. Maekawa, cond-mat/0501172.
- [27] R. Swirkowicz, M. Wilczynski, J. Barnas, cond-mat/0501605.
- [28] L.I.G lazman, M.E.Raikh, JETP Lett. 47, 452 (1988).
- [29] T.K.Ng, P.A.Lee, Phys. Rev. Lett. 61, 1768 (1988).
- [30] A.Kawabata, J.Phys.Soc.Japan 60, 3222 (1991).
- [31] Y.Meir, N.S.W ingreen, P.A.Lee, Phys. Rev. Lett. 66, 3048 (1991); Phys. Rev. Lett. 70, 2601 (1993).
- [32] S. Hersh eld, J. H. Davies, J. W. W ilkins, Phys. Rev. Lett. 67, 3720 (1991); Phys. Rev. B 46, 7046 (1992).
- [33] N.S.W ingreen, Y.Meir, Phys. Rev. B 49, 11 040 (1994).
- [34] M.Krawiec, K.I.W ysokinski, Phys. Rev. B 66, 165408 (2002).
- [35] D.Goldhaber-Gordon, H.Shtrikman, D.Mahalu, D.Abusch-Magder, U.Meirav, M.A.Kastner, Nature 391, 156 (1998).
- [36] S.M. Cronenwett, T.H. Oosterkamp, L.P.Kouwenhoven, Science 281, 540 (1998).
- [37] J. Schm id, J.W eis, K. Eberl, K. von K litzing, Physica B 256-258, 182 (1998); Phys. Rev. Lett.

84,5824 (2000).

- [38] F. Simmel, R.H. Blick, J.P. Kotthaus, W. Wegscheider, M. Bichler, Phys. Rev. Lett. 83, 804 (1999).
- [39] S. Sasaki, S. De Franceschi, J. M. Elzerman, W. G. van der Wiel, M. Eto, S. Tarucha, L. P. Kouwenhoven, Nature 405, 764 (2000).
- [40] S.Kirchner, L.Zhu, Q.Si, D.Natelson, Proc.Natl. A cad. Sci. USA 102, 18824 (2005).
- [41] P.Coleman, Phys. Rev. B 29, 3035 (1984).
- [42] J.C.LeGiullou, E.Ragoucy, Phys. Rev. B 52, 2403 (1999).
- [43] H. Haug, A. P. Jauho, Quantum K inetics in Transport and Optics of Sem iconductors, Springer, Berlin (1996).
- [44] M.Krawiec, K.I.W ysokinski, Solid State Commun. 115, 141 (2000).
- [45] D. V. Averin, Yu. V. Nazarov, in Single Charge Tunneling, Eds. H. Grabert, M. H. Devoret, Plenum Press (1992), NATO ASI Series B 294, p. 217.